



**1SS355** 



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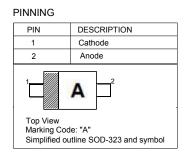
## Silicon Epitaxial Planar Switching Diode

#### Features

Small plastic package suitable

for surface mounted design

• High reliability with high surge current handling capability



### Applications

High speed switching

#### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RM</sub>	90	V
Reverse Voltage	V <sub>R</sub>	80	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	100	mA
Peak Forward Current	I <sub>FM</sub>	225	mA
Surge Forward Current (1 s)	I <sub>FSM</sub>	500	mA
Junction Temperature	Tj	150	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 150	٥C

#### Electrical Characteristics (T<sub>a</sub> = 25 °C)

Parameter	Symbol	Max.	Unit
Forward Voltage at I <sub>F</sub> = 100 mA	VF	1.2	V
Reverse Current at V <sub>R</sub> = 80 V	I <sub>R</sub>	0.1	μA
Capacitance between Terminals at $V_R$ = 0.5 V, f = 1 MHz	Ст	3	pF
Reverse Recovery Time at V <sub>R</sub> = 6 V, I <sub>F</sub> = 10 mA, R <sub>L</sub> = 100 $\Omega$	t <sub>rr</sub>	4	ns

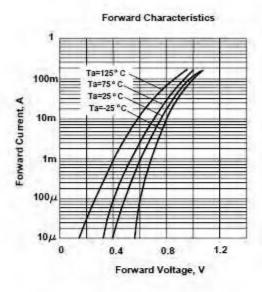


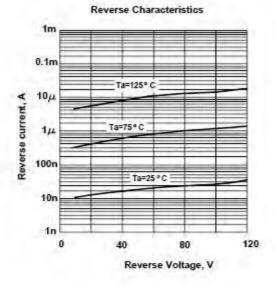
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#### Capacitance between terminals characteristics

